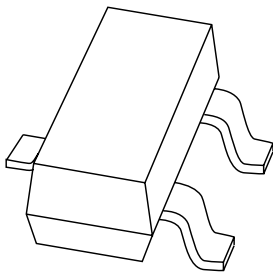


DATA SHEET



BSS63 PNP high-voltage transistor

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 16

PNP high-voltage transistor

BSS63

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 100 V).

APPLICATIONS

- High-voltage general purpose
- Switching applications.

DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.
NPN complement: BSS64.

MARKING

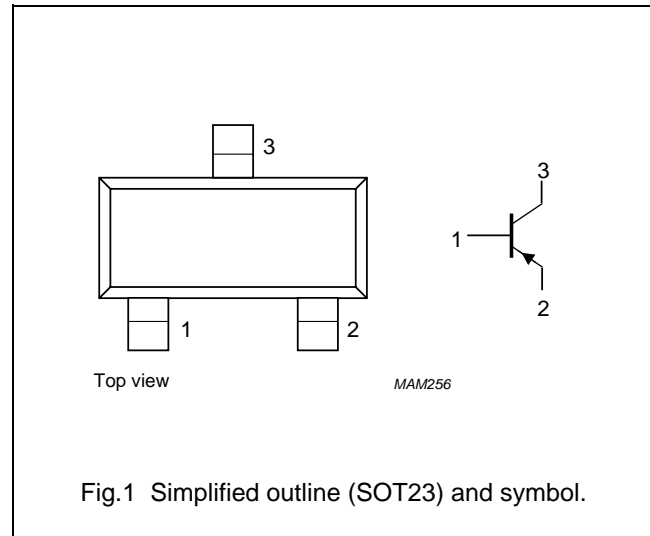
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSS63	BM*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSS63	-	plastic surface mounted package; 3 leads	SOT23

PNP high-voltage transistor

BSS63

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–110	V
V_{CEO}	collector-emitter voltage	open base	–	–100	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–100	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -90\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -90\text{ V}; T_j = 150\text{ °C}$	–	–	–50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -6\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -10\text{ mA}; V_{CE} = -1\text{ V}$	30	–	–	
		$I_C = -25\text{ mA}; V_{CE} = -1\text{ V}$	30	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$	–	–	–250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$	–	–	–900	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	3	–	pF
f_T	transition frequency	$I_C = -25\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	50	85	–	MHz

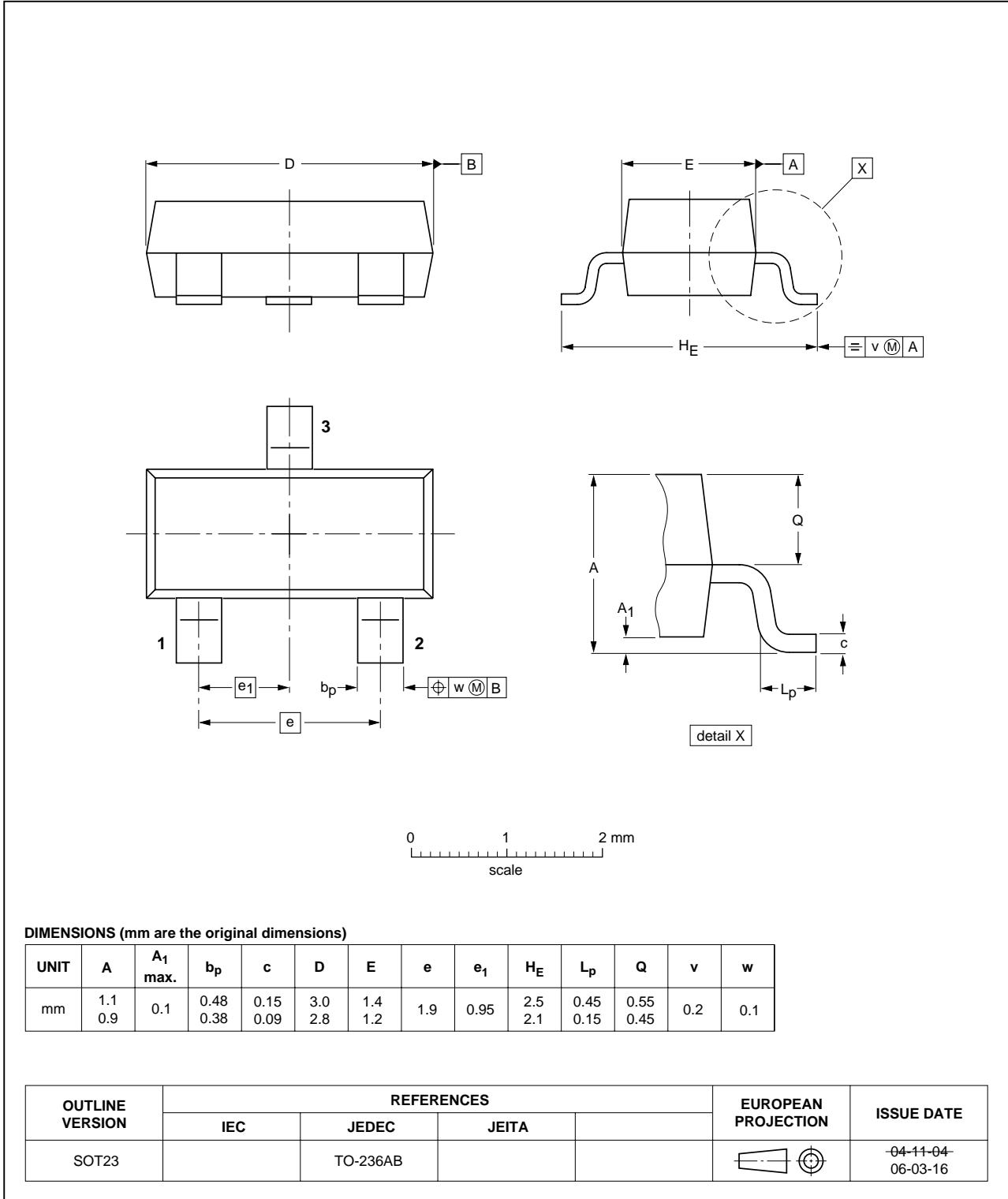
PNP high-voltage transistor

BSS63

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



PNP high-voltage transistor

BSS63

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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